

# BRDBC847

Rev.E Jul.-2023

SOT-363  
Package.

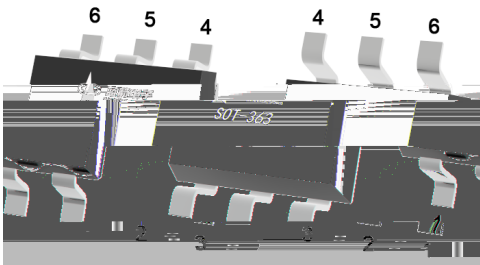
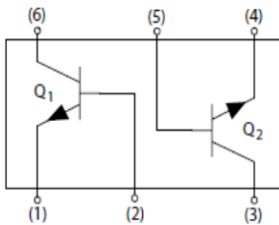
NPN

Double silicon NPN transistor in a SOT-363 Plastic

, BRDBC857

High voltage, complementary pair with BRDBC857, HF Product.

General purpose high voltage amplifier.



PIN 1 4 Emitter

PIN 2 5 Base

PIN 3 6 Collector

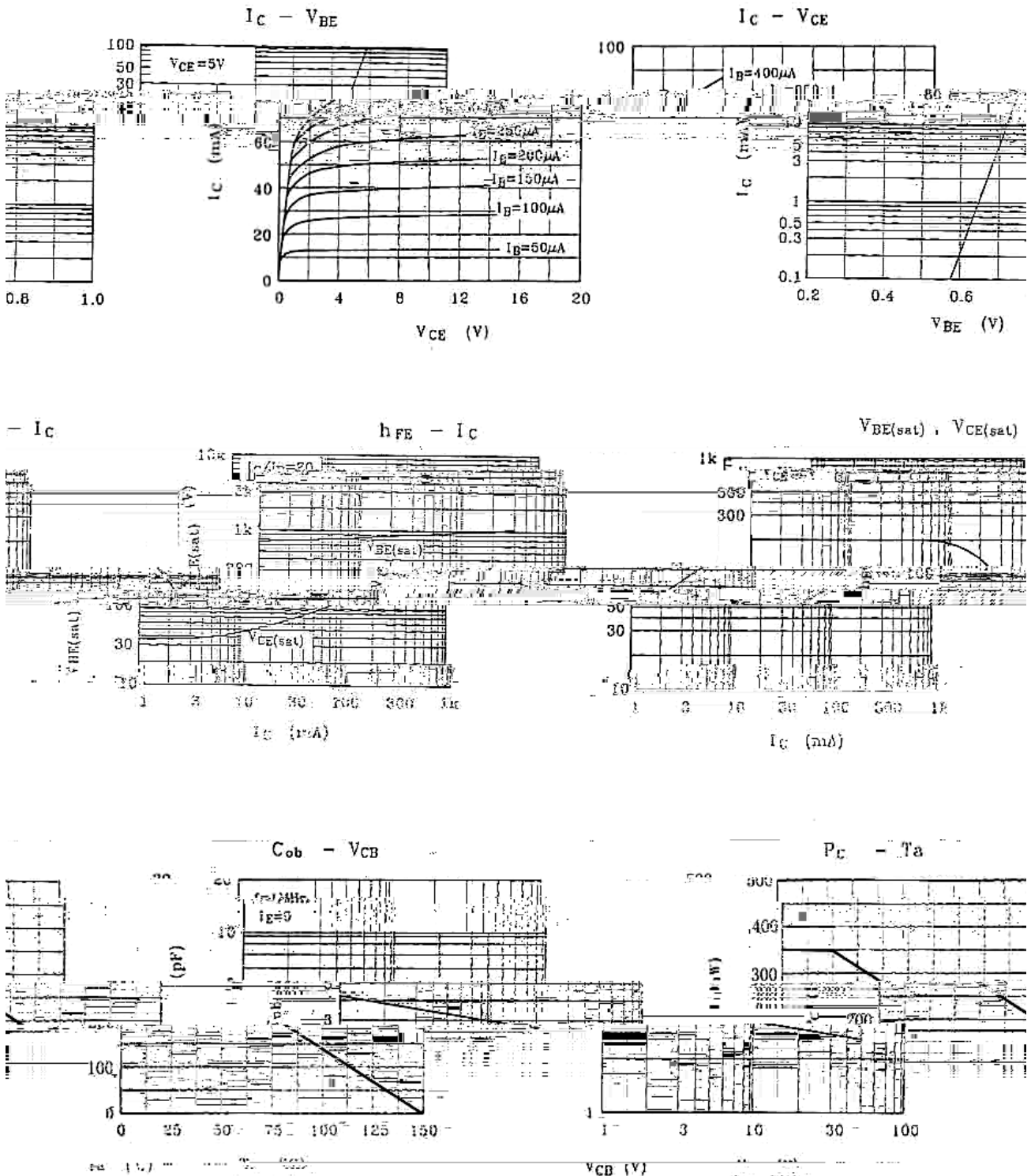
## / Absolute Maximum Ratings(Ta=25 )

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V <sub>CBO</sub>	50	V
Collector to Emitter Voltage	V <sub>CEO</sub>	45	V
Emitter to Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	100	mA
Total Package Dissipation	P <sub>D</sub>	380	mW
Thermal Resistance, Junction to Ambient	R <sub>JA</sub>	328	/W
Junction Temperature	T <sub>j</sub>	-55~+150	
Storage Temperature Range	T <sub>stg</sub>	-55~+150	

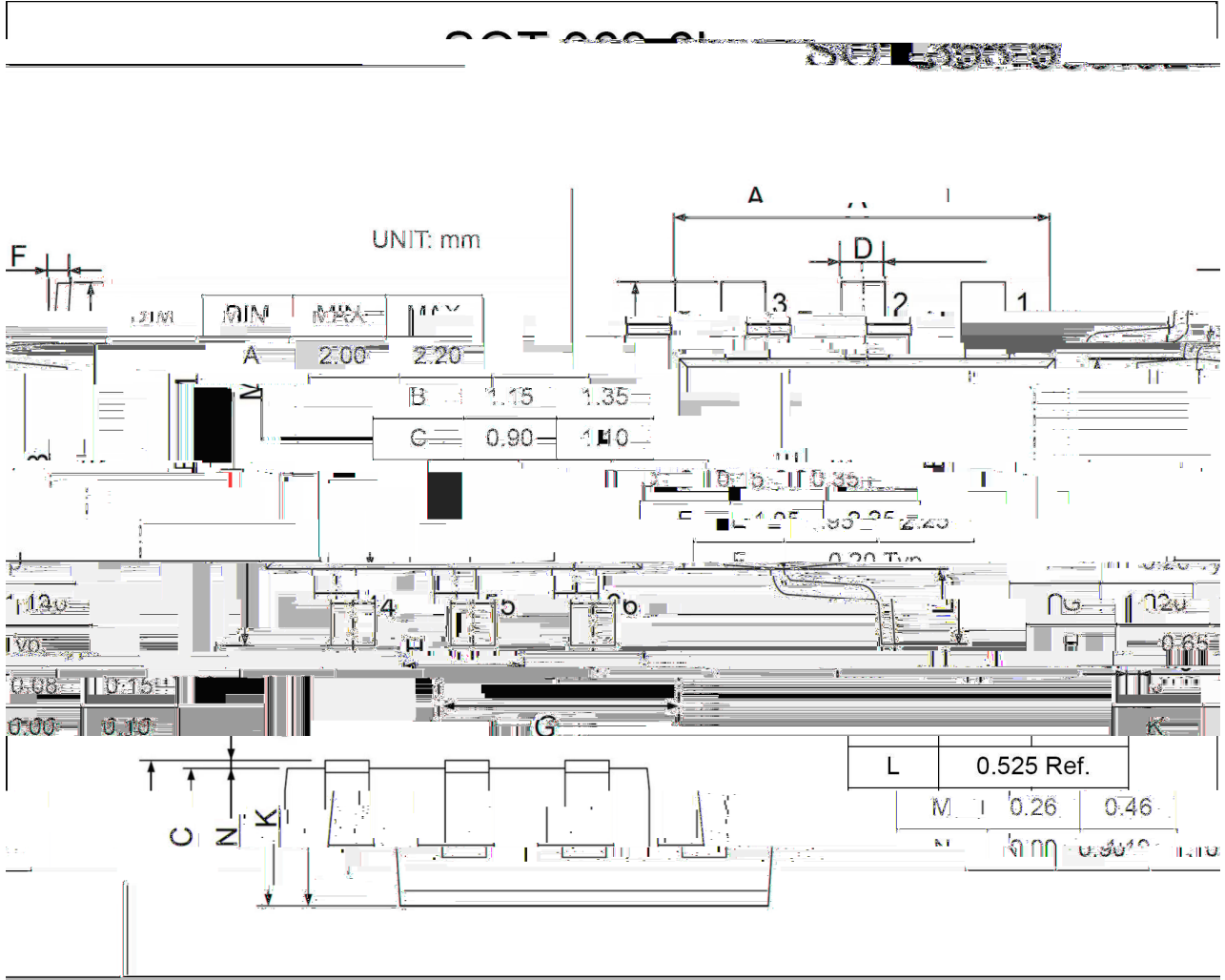
## / Electrical Characteristics(Ta=25 )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	V <sub>CBO</sub>	I <sub>C</sub> = 10μA I <sub>E</sub> = 0	50			V
Collector Emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> = 10mA I <sub>B</sub> = 0	45			V
Emitter Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> = 10μA I <sub>C</sub> = 0	6.0			V
Collector Emitter Breakdown Voltage	V <sub>CES</sub>	I <sub>C</sub> = 10μA V <sub>EB</sub> = 0	50			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 30V I <sub>E</sub> = 0			15	nA
		V <sub>CB</sub> = 30V I <sub>E</sub> = 0 T <sub>A</sub> = 150°C			5.0	A
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5.0V I <sub>C</sub> = 2.0mA	110		800	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA I <sub>B</sub> = 0.5mA			0.25	V
		I <sub>C</sub> = 100mA I <sub>B</sub> = 5.0mA			0.60	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 10mA I <sub>B</sub> = 0.5mA		0.70		V
		I <sub>C</sub> = 100mA I <sub>B</sub> = 5.0mA		0.90		V
Base-Emitter Voltage	V <sub>BE(on)</sub>	I <sub>C</sub> = 2.0mA V <sub>CE</sub> = 5.0V	580	660	700	mV
		I <sub>C</sub> = 10mA V <sub>CE</sub> = 5.0V			770	mV
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = 5.0V I <sub>C</sub> = 10mA f = 100MHz	100			MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V f = 1.0MHz			4.5	pF
Noise Figure	NF	I <sub>C</sub> = 0.2mA V <sub>CE</sub> = 5.0V R <sub>S</sub> = 2.0k f = 1.0kHz BW = 200Hz			10	dB

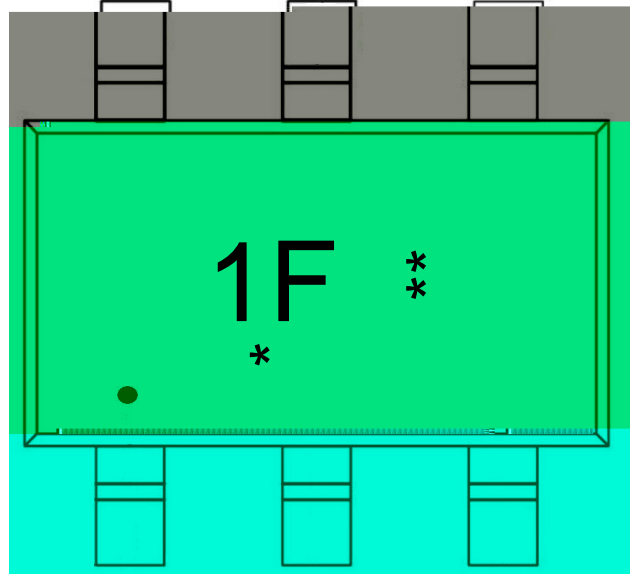
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



● " 1"

1

F hFE

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Note:

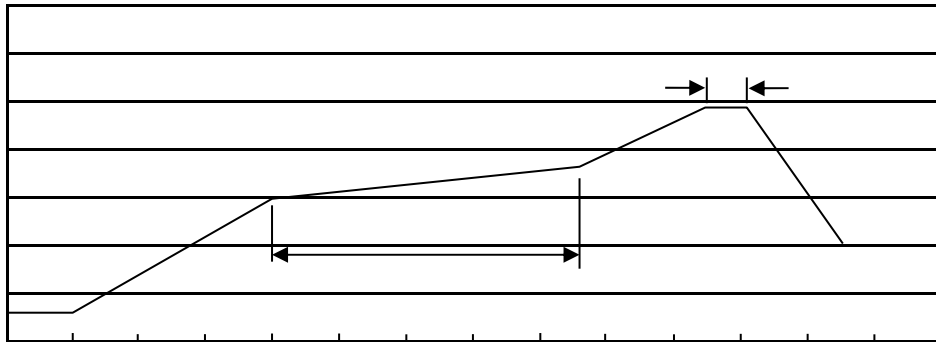
● " 1" Pin

1 Product Type Code

F hFE Classifications Symbol Code

\*\*\* Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- |   |       |     |           |          |   |
|---|-------|-----|-----------|----------|---|
| 1 | 150   | 180 | 60        | 90sec;   | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245±5 |     | 5±0.5sec; |          | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |       |     | 2         | 10 /sec. | 3. Cooling Speed: 2~10 /sec.            |

/ Resistance to Soldering Heat Test Conditions

260±5                      10±1 sec.                      Temp.:260±5                      Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm <sup>3</sup> )		
SOT-363	3,000	10	30,000	6	180,000	7" x8	180x120x180	390x385x205

/ Notices